

UNITED STATES PATENT AND TRADEMARK OFFICE

BEFORE THE PATENT TRIAL AND APPEAL BOARD

TAIWAN SEMICONDUCTOR MANUFACTURING CO., LTD,
Petitioner,

v.

GODO KAISHA IP BRIDGE 1,
Patent Owner.

IPR2017-01843¹
Patent 7,893,501

PATENT OWNER'S UPDATED EXHIBIT LIST

¹ Case IPR2017-01842 has been consolidated with this proceeding.

Exhibit	Description
2201	Request for Continued Examination dated March 29, 2010
2202	U.S. Patent No. 6,437,404 (“Xiang”)
2203	U.S. Patent No. 6,870,230 (“Matsuda”)
2204	Office Action dated May 10, 2010
2205	U.S. Patent No. 3,390,022
2206	McGraw-Hill Dictionary of Scientific and Technical Terms (2003)
2207	Declaration of Joshua J. Miller in Support of Motion for Admission <i>Pro Hac Vice</i>
2208	Declaration of Alexander D. Glew, Ph.D., P.E.
2209	Transcript of the Deposition of Stanley R. Shanfield, Ph.D. (March 27, 2018)
2210	Transcript of the Deposition of Stanley R. Shanfield, Ph.D. (March 28, 2018)
2211	Exhibit 2001 from March 27-28 Deposition of Dr. Stanley Shanfield, Ph.D., annotated version of '501 Patent
2212	Exhibit 2001 from March 27-28 Deposition of Dr. Stanley Shanfield, Ph.D., annotated version of Igarashi
2213	Exhibit 2003 from March 27-28 Deposition of Dr. Stanley Shanfield, Ph.D., Hawley’s Condensed Chemical Dictionary, Twelfth Edition (1993)
2214	Exhibit 2004 from March 27-28 Deposition of Dr. Stanley Shanfield, Ph.D., annotated version of Xiang (Ex. 2202)
2215	Exhibit 2005 from March 27-28 Deposition of Dr. Stanley Shanfield, Ph.D., annotated versions of Fig. 12 of Igarashi
2216	Exhibit 2006 from March 27-28 Deposition of Dr. Stanley Shanfield, Ph.D., annotated versions of Fig. 12 of Igarashi
2217	U.S. Pat. No. 6,924,237
2218	U.S. Pub. No. 2004/0164359
2219	U.S. Pat. No. 4,908,324
2220	U.S. Pat. No. 5,792,695
2221	U.S. Pat. No. 6,020,233
2222	Park, <i>et al.</i> , <i>A Study on Modified Silicon Surface after CHF₃/C₂F₆ Reactive Ion Etching</i> , 16 ETRI Journal 45 (1994)
2223	Miyatake, <i>et al.</i> , <i>Surface Contamination Control During Plasma Etching</i> , 1593 SPIE 47 (1991)
2224	Kastenmeier, <i>et al.</i> , <i>Gas Utilization in Remote Plasma Cleaning and Stripping Applications</i> , 18(5) J. VAC. SCI. TECH. 2102 (2000)
2225	Butterbaugh, <i>et al.</i> , <i>Plasma-Surface Interactions in Fluorocarbon</i>

Exhibit	Description
	<i>Etching of Silicon Dioxide</i> , 9(3) J. VAC. SCI. TECH. 1461 (1991)
2226	Schaepkens, <i>et al.</i> , <i>Study of the SiO₂-to-Si₃N₄ Etch Selectivity Mechanism in Inductively Coupled Fluorocarbon Plasmas and a Comparison with the SiO₂-to-Si Mechanism</i> , 17(1) J. VAC. SCI. TECH. 26 (1999)
2227	U.S. Patent No. 5,505,816
2228	The American Heritage College Dictionary (Third Edition)
2229	Curriculum vitae of Alexander D. Glew, Ph.D., P.E.
2230	Transcript of July 19, 2018 Conference Call
2231	Exhibit to Deposition of Stanley R. Shanfield, Ph.D.
2232	Deposition Transcript of Stanley R. Shanfield, Ph.D. July 25, 2018

CERTIFICATE OF SERVICE UNDER 37 C.F.R. §42.6 (e)(4)

I certify that on August 9, 2018 I will cause a copy of the foregoing document, including any exhibits referred to therein, to be served via electronic mail, as previously consented to by Petitioner, upon the following:

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Date: August 9, 2018

/MacAulay Rush/

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